

# Stopping for Ion : **H** , Target = **As**

<b>Pub. Year</b>	<b>Authors, Title, Journal Citation and Comments</b>	<b>Citation Numb</b>
<b>1968</b>	Sattler, A. R. Dearnaley, G. 'Channeling in Diamond-Type and Zinc-Blende Lattices: Comparative Effects in Channeling of Protons and Deuterons in Ge, GaAs, and Si' <i>Phys. Rev.</i> , 161, 244-52 (1967)(Erratum, <i>Phys. Rev.</i> , 165, 750 (1968)) <i>Comment</i> : S. 4-7.6 MeV H, D -> Ge, GaAs, Si (All Cryst.)	1968-Satt 0308
<b>1968</b>	Sattler, A. R. Vook, F. L. 'Channeling in Zinc-Blende Lattices: Energy-Loss Studies for Hydrogen and Helium Ions in InAs, GaSb, AlSb, and InSb' <i>Phys. Rev.</i> , 175, 526-32 (1968) <i>Comment</i> : S. (2-8 MeV) H, D, He, -> InAs, GaSb, InSb, AlSb (All (Cryst.))	1968-Satt2 0601
<b>1996</b>	Misdaq, M. A. Ellassali, R. 'Average Stopping Powers for Channeled Ions using Computational and Experimental Methods' <i>Nucl. Inst. Methods</i> , 119, 325-330 (1996) <i>Comment</i> : S. Light ions -> Si, GaAs (channeled)	1996-Misd 0964
<b>1996</b>	Rajatora, M. Vakevainen, K. Ahlgren, T. Rauhala, E. Raisanen, J. 'Stopping Powers of GaAs for 0.3-2.5 MeV H and He Ions' <i>Nucl. Inst. Methods</i> , B119, 457-462 (1996) <i>Comment</i> : S. H, He (0.3-2.5 MeV) -> GaAs	1996-Raja 2165